

Quad-Channel Digital Isolators ADuM2400/ADuM2401/ADuM2402

FEATURES

Low power operation **5 V operation** 1.0 mA per channel maximum @ 0 Mbps to 2 Mbps 3.5 mA per channel maximum @ 10 Mbps 31 mA per channel maximum @ 90 Mbps **3 V operation** 0.7 mA per channel maximum @ 0 Mbps to 2 Mbps 2.1 mA per channel maximum @ 10 Mbps 20 mA per channel maximum @ 90 Mbps **Bidirectional communication** 3 V/5 V level translation High temperature operation: 105°C High data rate: dc to 90 Mbps (NRZ) **Precise timing characteristics** 2 ns maximum pulse width distortion 2 ns maximum channel-to-channel matching High common-mode transient immunity: >25 kV/µs **Output enable function** 16-lead SOIC wide body package (RoHS compliant) Safety and regulatory approvals UL recognition: 5000 V rms for 1 minute per UL 1577 **CSA Component Acceptance Notice #5A** IEC 60950-1: 600 V rms (reinforced) IEC 60601-1: 250 V rms (reinforced) **VDE Certificate of Conformity** DIN V VDE V 0884-10 (VDE V 0884-10):2006-12 VIORM = 846 V peak

APPLICATIONS

General-purpose, high voltage, multichannel isolation **Medical equipment Motor drives Power supplies**

GENERAL DESCRIPTION

The ADuM240x1 are 4-channel digital isolators based on Analog Devices, Inc., iCoupler® technology. Combining high speed CMOS and monolithic air core transformer technology, these isolation components provide outstanding performance characteristics that are superior to alternatives, such as optocoupler devices.

By avoiding the use of LEDs and photodiodes, *i*Coupler devices remove the design difficulties commonly associated with optocouplers. The typical optocoupler concerns regarding uncertain current transfer ratios, nonlinear transfer functions, and

temperature and lifetime effects are eliminated with the simple

¹ Protected by U.S. Patents 5,952,849; 6,873,065; and 7,075,329. Other patents pending.

Rev. C

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FUNCTIONAL BLOCK DIAGRAMS

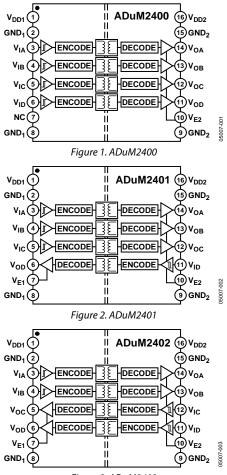


Figure 3. ADuM2402

*i*Coupler digital interfaces and stable performance characteristics. Furthermore, *i*Coupler devices run at one-tenth to one-sixth the power of optocouplers at comparable signal data rates.

The ADuM240x isolators provide four independent isolation channels in a variety of channel configurations and data rates (see the Ordering Guide). The ADuM240x models operate with the supply voltage of either side ranging from 2.7 V to 5.5 V, providing compatibility with lower voltage systems as well as enabling a voltage translation functionality across the isolation barrier. In addition, the ADuM240x provide low pulse width distortion (<2 ns for CRWZ grade) and tight channel-to-channel matching (<2 ns for CRWZ grade). Unlike other optocoupler alternatives, the ADuM240x isolators have a patented refresh feature that ensures dc correctness in the absence of input logic transitions and during power-up/power-down conditions.

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9/05—Revision 0: Initial Version

SPECIFICATIONS

ELECTRICAL CHARACTERISTICS—5 V OPERATION¹

 $4.5 \text{ V} \le V_{DD1} \le 5.5 \text{ V}, 4.5 \text{ V} \le V_{DD2} \le 5.5 \text{ V}.$ All minimum/maximum specifications apply over the entire recommended operation range, unless otherwise noted. All typical specifications are at $T_A = 25^{\circ}$ C, $V_{DD1} = V_{DD2} = 5 \text{ V}.$

Parameter	Symbol	Min	Тур	Max	Unit	Test Conditions
DC SPECIFICATIONS	Symbol		176	тих	0	
Input Supply Current per Channel, Quiescent	IDDI (Q)		0.50	0.53	mA	
Output Supply Current per Channel, Quescent			0.19	0.21	mA	
ADuM2400 Total Supply Current, Four Channels ²	1000 (Q)		0.15	0.21	110.	
DC to 2 Mbps						
V _{DD1} Supply Current	IDD1 (Q)		2.2	2.8	mA	DC to 1 MHz logic signal frequency
V _{DD2} Supply Current			0.9	1.4	mA	DC to 1 MHz logic signal frequency
10 Mbps (BRWZ and CRWZ Grades Only)	1002 (Q)		0.9	1.7	11173	
V _{DD1} Supply Current	IDD1 (10)		8.6	10.6	mA	5 MHz logic signal frequency
V _{DD2} Supply Current	IDD1 (10)		2.6	3.5	mA	5 MHz logic signal frequency
90 Mbps (CRWZ Grade Only)	1002 (10)		2.0	5.5	110.	5 Milz logic signal frequency
V _{DD1} Supply Current	I _{DD1 (90)}		70	100	mA	45 MHz logic signal frequency
V _{DD2} Supply Current	IDD1 (90)		18	25	mA	45 MHz logic signal frequency
ADuM2401 Total Supply Current, Four Channels ²	1002 (90)		10	25	11173	
DC to 2 Mbps						
V _{DD1} Supply Current			1.8	2.4	mA	DC to 1 MHz logic signal frequency
V _{DD1} Supply Current	DD1 (Q)		1.0	2.4 1.8	mA	DC to 1 MHz logic signal frequency
10 Mbps (BRWZ and CRWZ Grades Only)	DD2 (Q)		1.2	1.0	ШA	
			71	0.0		E MUT logic signal fragman or
V _{DD1} Supply Current	DD1 (10)		7.1 4.1	9.0	mA	5 MHz logic signal frequency 5 MHz logic signal frequency
V _{DD2} Supply Current	I _{DD2 (10)}		4.1	5.0	mA	
90 Mbps (CRWZ Grade Only)			F7	07		45 MUT logic signal frequency
V _{DD1} Supply Current	DD1 (90)		57	82	mA	45 MHz logic signal frequency
V _{DD2} Supply Current	DD2 (90)		31	43	mA	45 MHz logic signal frequency
ADuM2402 Total Supply Current, Four Channels ²						
DC to 2 Mbps				~ 1		
V _{DD1} or V _{DD2} Supply Current	I _{DD1 (Q)} , I _{DD2 (Q)}		1.5	2.1	mA	DC to 1 MHz logic signal frequency
10 Mbps (BRWZ and CRWZ Grades Only)						
V _{DD1} or V _{DD2} Supply Current	I _{DD1 (10)} , I _{DD2 (10)}		5.6	7.0	mA	5 MHz logic signal frequency
90 Mbps (CRWZ Grade Only)						
V _{DD1} or V _{DD2} Supply Current	I _{DD1 (90)} , I _{DD2 (90)}		44	62	mA	45 MHz logic signal frequency
For All Models						
Input Currents	IIA, IIB, IIC,	-10	+0.01	+10	μΑ	$0 V \leq V_{IA}, V_{IB}, V_{IC}, V_{ID} \leq V_{DD1} \text{ or } V_{DD2},$
the statistic terms of the sector terms	IID, IE1, IE2	2.0				$0 V \leq V_{\text{E1}}, V_{\text{E2}} \leq V_{\text{DD1}} \text{ or } V_{\text{DD2}}$
Logic High Input Threshold	Vih, Veh	2.0		0.0	V	
Logic Low Input Threshold	VIL, VEL			0.8	V	
Logic High Output Voltages	Voah, Vobh, Voch, Vodh	(V _{DD1} or V _{DD2}) – 0.1			V	$I_{\text{Ox}} = -20 \ \mu\text{A}, V_{\text{Ix}} = V_{\text{IxH}}$
		$(V_{DD1} \text{ or } V_{DD2}) - 0.4$			V	$I_{\text{Ox}} = -4 \text{ mA}, V_{\text{Ix}} = V_{\text{IxH}}$
Logic Low Output Voltages	VOAL, VOBL,		0.0	0.1	V	$I_{Ox} = 20 \ \mu\text{A}, V_{Ix} = V_{IxL}$
	V _{OCL} , V _{ODL}		0.04	0.1	V	$I_{\text{Ox}} = 400 \ \mu\text{A}, \ V_{\text{Ix}} = V_{\text{IxL}}$
			0.2	0.4	V	$I_{\text{Ox}} = 4 \text{ mA}, V_{\text{Ix}} = V_{\text{IxL}}$
SWITCHING SPECIFICATIONS						
ADuM240xARWZ						
Minimum Pulse Width ³	PW			1000		$C_L = 15 \text{ pF}$, CMOS signal levels
Maximum Data Rate ⁴		1			Mbps	$C_L = 15 \text{ pF}$, CMOS signal levels
Propagation Delay ⁵	tphl, tplh	50	65	100	ns	$C_L = 15 \text{ pF}$, CMOS signal levels
Pulse Width Distortion, $ t_{PLH} - t_{PHL} ^5$	PWD			40	ns	$C_L = 15 \text{ pF}$, CMOS signal levels
Propagation Delay Skew ⁶	t _{PSK}			50	ns	$C_L = 15 \text{ pF}$, CMOS signal levels
Channel-to-Channel Matching ⁷	$t_{\text{PSKCD}}/t_{\text{PSKOD}}$			50	ns	$C_L = 15 \text{ pF}$, CMOS signal levels

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Parameter	Symbol	Min	Тур	Мах	Unit	Test Conditions
ADuM240xBRWZ						
Minimum Pulse Width ³	PW			100	ns	$C_L = 15 \text{ pF}$, CMOS signal levels
Maximum Data Rate ⁴		10			Mbps	$C_L = 15 \text{ pF}$, CMOS signal levels
Propagation Delay ⁵	tphl, tplh	20	32	50	ns	$C_L = 15 \text{ pF}$, CMOS signal levels
Pulse Width Distortion, t _{PLH} – t _{PHL} ⁵	PWD			3	ns	C _L = 15 pF, CMOS signal levels
Change vs. Temperature			5		ps/°C	$C_L = 15 \text{ pF}$, CMOS signal levels
Propagation Delay Skew ⁶	t _{PSK}			15	ns	$C_L = 15 \text{ pF}$, CMOS signal levels
Channel-to-Channel Matching, Codirectional Channels ⁷	t _{PSKCD}			3	ns	$C_L = 15 \text{ pF}$, CMOS signal levels
Channel-to-Channel Matching, Opposing-Directional Channels ⁷	t _{PSKOD}			6	ns	$C_L = 15 \text{ pF}$, CMOS signal levels
ADuM240xCRWZ						
Minimum Pulse Width ³	PW		8.3	11.1	ns	$C_L = 15 \text{ pF}$, CMOS signal levels
Maximum Data Rate ⁴		90	120		Mbps	C _L = 15 pF, CMOS signal levels
Propagation Delay ⁵	tphl, tplh	18	27	32	ns	$C_L = 15 \text{ pF}$, CMOS signal levels
Pulse Width Distortion, tplh – tphl ⁵	PWD		0.5	2	ns	C _L = 15 pF, CMOS signal levels
Change vs. Temperature			3		ps/°C	$C_L = 15 \text{ pF}$, CMOS signal levels
Propagation Delay Skew ⁶	t _{PSK}			10	ns	C _L = 15 pF, CMOS signal levels
Channel-to-Channel Matching, Codirectional Channels ⁷	t _{PSKCD}			2	ns	$C_L = 15 \text{ pF}$, CMOS signal levels
Channel-to-Channel Matching, Opposing-Directional Channels ⁷	t _{PSKOD}			5	ns	$C_L = 15 \text{ pF}$, CMOS signal levels
For All Models						
Output Disable Propagation Delay (High/Low to High Impedance)	tphz, tplh		6	8	ns	$C_L = 15 \text{ pF}$, CMOS signal levels
Output Enable Propagation Delay (High Impedance to High/Low)	t _{PZH} , t _{PZL}		6	8	ns	$C_L = 15 \text{ pF}$, CMOS signal levels
Output Rise/Fall Time (10% to 90%)	t _R /t _F		2.5		ns	C _L = 15 pF, CMOS signal levels
Common-Mode Transient Immunity at Logic High Output ⁸	CM _H	25	35		kV/μs	$V_{lx} = V_{DD1}$ or V_{DD2} , $V_{CM} = 1000$ V, transient magnitude = 800 V
Common-Mode Transient Immunity at Logic Low Output ⁸	CM∟	25	35		kV/μs	$V_{lx} = 0 V, V_{CM} = 1000 V,$ transient magnitude = 800 V
Refresh Rate	f _r		1.2		Mbps	
Input Dynamic Supply Current per Channel ⁹	I _{DDI (D)}		0.19		mA/Mbps	
Output Dynamic Supply Current per Channel ⁹	I _{DDO (D)}		0.05		mA/Mbps	

¹ All voltages are relative to their respective ground.

² Supply current values are for all four channels combined running at identical data rates. Output supply current values are specified with no output load present. The supply current associated with an individual channel operating at a given data rate can be calculated as described in the Power Consumption section. See Figure 8 through Figure 10 for information on per channel supply current as a function of data rate for unloaded and loaded conditions. See Figure 11 through Figure 15 for total V_{DD1} and V_{DD2} supply currents as a function of data rate for ADuM2400/ADuM2401/ADuM2402 channel configurations.

³ The minimum pulse width is the shortest pulse width at which the specified pulse width distortion is guaranteed.

⁴ The maximum data rate is the fastest data rate at which the specified pulse width distortion is guaranteed.

⁵ t_{PHL} propagation delay is measured from the 50% level of the falling edge of the V_{Ix} signal to the 50% level of the falling edge of the V_{ox} signal. t_{PLH} propagation delay is measured from the 50% level of the rising edge of the V_{ix} signal to the 50% level of the rising edge of the V_{ox} signal.

⁶ t_{PSK} is the magnitude of the worst-case difference in t_{PHL} or t_{PLH} that is measured between units at the same operating temperature, supply voltages, and output load within the recommended operating conditions.

⁷ Codirectional channel-to-channel matching is the absolute value of the difference in propagation delays between any two channels with inputs on the same side of the isolation barrier. Opposing directional channel-to-channel matching is the absolute value of the difference in propagation delays between any two channels with inputs on opposing sides of the isolation barrier.

⁸ CM_H is the maximum common-mode voltage slew rate that can be sustained while maintaining V₀ > 0.8 V_{DD2}. CM_L is the maximum common-mode voltage slew rate that can be sustained while maintaining V₀ < 0.8 V. The common-mode voltage slew rates apply to both rising and falling common-mode voltage edges. The transient magnitude is the range over which the common mode is slewed.</p>

⁹ Dynamic supply current is the incremental amount of supply current required for a 1 Mbps increase in signal data rate. See Figure 8 through Figure 10 for information on per channel supply current for unloaded and loaded conditions. See the Power Consumption section for guidance on calculating per channel supply current for a given data rate.

ELECTRICAL CHARACTERISTICS—3 V OPERATION¹

 $2.7 \text{ V} \le \text{V}_{\text{DD1}} \le 3.6 \text{ V}, 2.7 \text{ V} \le \text{V}_{\text{DD2}} \le 3.6 \text{ V}$. All minimum/maximum specifications apply over the entire recommended operation range, unless otherwise noted. All typical specifications are at $T_{\rm A}$ = 25°C, $V_{\rm DD1}$ = $V_{\rm DD2}$ = 3.0 V.

Table 2.						
Parameter	Symbol	Min	Тур	Мах	Unit	Test Conditions
DC SPECIFICATIONS						
Input Supply Current per Channel, Quiescent	I _{DDI (Q)}		0.26	0.31	mA	
Output Supply Current per Channel, Quiescent	I _{DDO (Q)}		0.11	0.14	mA	
ADuM2400 Total Supply Current, Four Channels ²						
DC to 2 Mbps						
VDD1 Supply Current	I _{DD1 (Q)}		1.2	1.9	mA	DC to 1 MHz logic signal frequency
V _{DD2} Supply Current	I _{DD2 (Q)}		0.5	0.9	mA	DC to 1 MHz logic signal frequency
10 Mbps (BRWZ and CRWZ Grades Only)						
VDD1 Supply Current	I _{DD1 (10)}		4.5	6.5	mA	5 MHz logic signal frequency
V _{DD2} Supply Current	I _{DD2 (10)}		1.4	2.0	mA	5 MHz logic signal frequency
90 Mbps (CRWZ Grade Only)						
VDD1 Supply Current	I _{DD1 (90)}		37	65	mA	45 MHz logic signal frequency
V _{DD2} Supply Current	I _{DD2 (90)}		11	15	mA	45 MHz logic signal frequency
ADuM2401 Total Supply Current, Four Channels ²						
DC to 2 Mbps						
VDD1 Supply Current	I _{DD1 (Q)}		1.0	1.6	mA	DC to 1 MHz logic signal frequency
V _{DD2} Supply Current	I _{DD2 (Q)}		0.7	1.2	mA	DC to 1 MHz logic signal frequency
10 Mbps (BRWZ and CRWZ Grades Only)						
VDD1 Supply Current	I _{DD1 (10)}		3.7	5.4	mA	5 MHz logic signal frequency
VDD2 Supply Current	I _{DD2 (10)}		2.2	3.0	mA	5 MHz logic signal frequency
90 Mbps (CRWZ Grade Only)						
VDD1 Supply Current	I _{DD1 (90)}		30	52	mA	45 MHz logic signal frequency
VDD2 Supply Current	I _{DD2 (90)}		18	27	mA	45 MHz logic signal frequency
ADuM2402 Total Supply Current, Four Channels ²						
DC to 2 Mbps						
VDD1 or VDD2 Supply Current	I _{DD1 (Q)} , I _{DD2 (Q)}		0.9	1.5	mA	DC to 1 MHz logic signal frequency
10 Mbps (BRWZ and CRWZ Grades Only)						
VDD1 or VDD2 Supply Current	I _{DD1 (10)} , I _{DD2 (10)}		3.0	4.2	mA	5 MHz logic signal frequency
90 Mbps (CRWZ Grade Only)						
V _{DD1} or V _{DD2} Supply Current	I _{DD1 (90)} , I _{DD2 (90)}		24	39	mA	45 MHz logic signal frequency
For All Models						
Input Currents	IIA, IIB, IIC,	-10	+0.01	+10	μA	$0 \text{ V} \leq V_{IA}, V_{IB}, V_{IC}, V_{ID} \leq V_{DD1} \text{ or } V_{DD2},$
	$\mathbf{I}_{\text{ID}}, \mathbf{I}_{\text{E1}}, \mathbf{I}_{\text{E2}}$					$0~V \leq V_{\text{E1}}, V_{\text{E2}} \leq V_{\text{DD1}}~or~V_{\text{DD2}}$
Logic High Input Threshold	$V_{\text{IH}}, V_{\text{EH}}$	1.6			V	
Logic Low Input Threshold	V_{IL}, V_{EL}			0.4	V	
Logic High Output Voltages	V_{OAH} , V_{OBH} ,	$(V_{\text{DD1}} \text{ or } V_{\text{DD2}}) - 0.1$	3.0		V	$I_{\text{Ox}} = -20 \; \mu\text{A}, V_{\text{Ix}} = V_{\text{IxH}}$
	Voch, Vodh	$(V_{\text{DD1}} \text{ or } V_{\text{DD2}}) - 0.4$	2.8		V	$I_{Ox} = -4 \text{ mA}, V_{Ix} = V_{IxH}$
Logic Low Output Voltages	V _{OAL} , V _{OBL} ,		0.0	0.1	V	$I_{\text{Ox}} = 20 \ \mu\text{A}, \ V_{\text{Ix}} = V_{\text{IxL}}$
	Vocl, Vodl		0.04	0.1	V	$I_{\text{Ox}} = 400 \ \mu\text{A}, \ V_{\text{Ix}} = V_{\text{IxL}}$
			0.2	0.4	V	$I_{\text{Ox}} = 4 \text{ mA}, V_{\text{Ix}} = V_{\text{IxL}}$
SWITCHING SPECIFICATIONS						
ADuM240xARWZ						
Minimum Pulse Width ³	PW			1000	ns	C _L = 15 pF, CMOS signal levels
Maximum Data Rate ⁴		1			Mbps	$C_L = 15 \text{ pF}$, CMOS signal levels
Propagation Delay ⁵	tphl, tplh	50	75	100	ns	$C_L = 15 \text{ pF}$, CMOS signal levels
Pulse Width Distortion, $ t_{PLH} - t_{PHL} ^5$	PWD			40	ns	$C_L = 15 \text{ pF}$, CMOS signal levels
Propagation Delay Skew ⁶	t _{PSK}			50	ns	$C_L = 15 \text{ pF}$, CMOS signal levels
Channel-to-Channel Matching ⁷	tpskcd/tpskod			50	ns	$C_L = 15 \text{ pF}$, CMOS signal levels

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Parameter	Symbol	Min	Тур	Max	Unit	Test Conditions
ADuM240xBRWZ						
Minimum Pulse Width ³	PW			100	ns	$C_{L} = 15 \text{ pF}$, CMOS signal levels
Maximum Data Rate ⁴		10			Mbps	$C_L = 15 \text{ pF}$, CMOS signal levels
Propagation Delay ⁵	tphl, tplh	20	38	50	ns	$C_L = 15 \text{ pF}$, CMOS signal levels
Pulse Width Distortion, $ t_{PLH} - t_{PHL} ^5$	PWD			3	ns	$C_L = 15 \text{ pF}$, CMOS signal levels
Change vs. Temperature			5		ps/°C	$C_L = 15 \text{ pF}$, CMOS signal levels
Propagation Delay Skew ⁶	t _{PSK}			22	ns	$C_L = 15 \text{ pF}$, CMOS signal levels
Channel-to-Channel Matching, Codirectional Channels ⁷	t _{PSKCD}			3	ns	$C_L = 15 \text{ pF}$, CMOS signal levels
Channel-to-Channel Matching, Opposing-Directional Channels ⁷	t _{PSKOD}			6	ns	$C_L = 15 \text{ pF}$, CMOS signal levels
ADuM240xCRWZ						
Minimum Pulse Width ³	PW		8.3	11.1	ns	$C_{L} = 15 \text{ pF}$, CMOS signal levels
Maximum Data Rate ⁴		90	120		Mbps	$C_L = 15 \text{ pF}$, CMOS signal levels
Propagation Delay ⁵	tphl, tplh	20	34	45	ns	$C_{L} = 15 \text{ pF}$, CMOS signal levels
Pulse Width Distortion, tplh – tphl ⁵	PWD		0.5	2	ns	$C_{L} = 15 \text{ pF}$, CMOS signal levels
Change vs. Temperature			3		ps/°C	$C_L = 15 \text{ pF}$, CMOS signal levels
Propagation Delay Skew ⁶	t _{PSK}			16	ns	$C_{L} = 15 \text{ pF}$, CMOS signal levels
Channel-to-Channel Matching, Codirectional Channels ⁷	t pskcd			2	ns	$C_L = 15 \text{ pF}$, CMOS signal levels
Channel-to-Channel Matching, Opposing-Directional Channels ⁷	t PSKOD			5	ns	$C_L = 15 \text{ pF}$, CMOS signal levels
For All Models						
Output Disable Propagation Delay (High/Low to High Impedance)	tphz, tplh		6	8	ns	$C_L = 15 \text{ pF}$, CMOS signal levels
Output Enable Propagation Delay (High Impedance to High/Low)	t _{PZH} , t _{PZL}		6	8	ns	$C_L = 15 \text{ pF}$, CMOS signal levels
Output Rise/Fall Time (10% to 90%)	t _R /t _F		3		ns	C _L = 15 pF, CMOS signal levels
Common-Mode Transient Immunity at Logic High Output ⁸	CM _H	25	35		kV/μs	$V_{lx} = V_{DD1}$ or V_{DD2} , $V_{CM} = 1000$ V, transient magnitude = 800 V
Common-Mode Transient Immunity at Logic Low Output ⁸	CML	25	35		kV/μs	$V_{Ix} = 0 V, V_{CM} = 1000 V,$ transient magnitude = 800 V
Refresh Rate	f _r		1.1		Mbps	
Input Dynamic Supply Current per Channel ⁹	I _{DDI (D)}		0.10		mA/Mbps	
Output Dynamic Supply Current per Channel ⁹	I _{DDO (D)}		0.03		mA/Mbps	

¹ All voltages are relative to their respective ground.

² Supply current values are for all four channels combined running at identical data rates. Output supply current values are specified with no output load present. The supply current associated with an individual channel operating at a given data rate can be calculated as described in the Power Consumption section. See Figure 8 through Figure 10 for information on per channel supply current as a function of data rate for unloaded and loaded conditions. See Figure 11 through Figure 15 for total V_{DD1} and V_{DD2} supply currents as a function of data rate for ADuM2400/ADuM2401/ADuM2402 channel configurations.

³ The minimum pulse width is the shortest pulse width at which the specified pulse width distortion is guaranteed.

⁴ The maximum data rate is the fastest data rate at which the specified pulse width distortion is guaranteed.

⁵ t_{PHL} propagation delay is measured from the 50% level of the falling edge of the V_{Ix} signal to the 50% level of the falling edge of the V_{ox} signal. t_{PLH} propagation delay is measured from the 50% level of the rising edge of the V_{ix} signal to the 50% level of the rising edge of the V_{ox} signal.

⁶ t_{PSK} is the magnitude of the worst-case difference in t_{PHL} or t_{PLH} that is measured between units at the same operating temperature, supply voltages, and output load within the recommended operating conditions.

⁷ Codirectional channel-to-channel matching is the absolute value of the difference in propagation delays between any two channels with inputs on the same side of the isolation barrier. Opposing directional channel-to-channel matching is the absolute value of the difference in propagation delays between any two channels with inputs on opposing sides of the isolation barrier.

⁸ CM_H is the maximum common-mode voltage slew rate that can be sustained while maintaining V₀ > 0.8V_{DD2}. CM_L is the maximum common-mode voltage slew rate that can be sustained while maintaining V₀ < 0.8 V. The common-mode voltage slew rates apply to both rising and falling common-mode voltage edges. The transient magnitude is the range over which the common mode is slewed.</p>

⁹ Dynamic supply current is the incremental amount of supply current required for a 1 Mbps increase in signal data rate. See Figure 8 through Figure 10 for information on per channel supply current for unloaded and loaded conditions. See the Power Consumption section for guidance on calculating per channel supply current for a given data rate.

ELECTRICAL CHARACTERISTICS—MIXED 5 V/3 V OR 3 V/5 V OPERATION¹

5 V/3 V operation: $4.5 \text{ V} \le \text{V}_{\text{DD1}} \le 5.5 \text{ V}$, $2.7 \text{ V} \le \text{V}_{\text{DD2}} \le 3.6 \text{ V}$. 3 V/5 V operation: $2.7 \text{ V} \le \text{V}_{\text{DD1}} \le 3.6 \text{ V}$, $4.5 \text{ V} \le \text{V}_{\text{DD2}} \le 5.5 \text{ V}$. All minimum/maximum specifications apply over the entire recommended operation range, unless otherwise noted. All typical specifications are at $T_A = 25^{\circ}\text{C}$; $V_{\text{DD1}} = 3.0 \text{ V}$, $V_{\text{DD2}} = 5 \text{ V}$; or $V_{\text{DD1}} = 5 \text{ V}$, $V_{\text{DD2}} = 3.0 \text{ V}$.

Parameter	Symbol	Min	Тур	Max	Unit	Test Conditions
DC SPECIFICATIONS	-					
Input Supply Current per Channel, Quiescent	IDDI (Q)					
5 V/3 V Operation			0.50	0.53	mA	
3 V/5 V Operation			0.26	0.31	mA	
Output Supply Current per Channel, Quiescent	IDDO (Q)					
5 V/3 V Operation	(2)		0.11	0.14	mA	
3 V/5 V Operation			0.19	0.21	mA	
ADuM2400 Total Supply Current, Four Channels ²						
DC to 2 Mbps						
V _{DD1} Supply Current	IDD1 (Q)					
5 V/3 V Operation	1001 (Q)		2.2	2.8	mA	DC to 1 MHz logic signal frequence
3 V/5 V Operation			1.2	1.9	mA	DC to 1 MHz logic signal frequence
V _{DD2} Supply Current	IDD2 (Q)		1.2	1.2	1117 (
5 V/3 V Operation	1002 (Q)		0.5	0.9	mA	DC to 1 MHz logic signal frequenc
3 V/5 V Operation			0.9	1.4	mA	DC to 1 MHz logic signal frequence
10 Mbps (BRWZ and CRWZ Grades Only)			0.9	1.4	IIIA	
V _{DD1} Supply Current	lan. on					
5 V/3 V Operation	DD1 (10)		8.6	10.6	mA	5 MHz logic signal frequency
3 V/5 V Operation			8.0 4.5	6.5	mA	5 MHz logic signal frequency
-			4.5	0.5	IIIA	5 Miliziogie signal frequency
V _{DD2} Supply Current	DD2 (10)		1.4	2.0		
5 V/3 V Operation			1.4 2.6	2.0 3.5	mA mA	5 MHz logic signal frequency 5 MHz logic signal frequency
3 V/5 V Operation			2.0	5.5	IIIA	5 MHZ logic signal frequency
90 Mbps (CRWZ Grade Only)						
V _{DD1} Supply Current	DD1 (90)		70	100	mA	45 MUE logic signal from on ou
5 V/3 V Operation						45 MHz logic signal frequency
3 V/5 V Operation			37	65	mA	45 MHz logic signal frequency
V _{DD2} Supply Current	I _{DD2} (90)		1.1	15		
5 V/3 V Operation			11	15	mA	45 MHz logic signal frequency
3 V/5 V Operation			18	25	mA	45 MHz logic signal frequency
ADuM2401 Total Supply Current, Four Channels ²						
DC to 2 Mbps						
VDD1 Supply Current	DD1 (Q)					
5 V/3 V Operation			1.8	2.4	mA	DC to 1 MHz logic signal frequence
3 V/5 V Operation			1.0	1.6	mA	DC to 1 MHz logic signal frequence
VDD2 Supply Current	I _{DD2 (Q)}					
5 V/3 V Operation			0.7	1.2	mA	DC to 1 MHz logic signal frequence
3 V/5 V Operation			1.2	1.8	mA	DC to 1 MHz logic signal frequence
10 Mbps (BRWZ and CRWZ Grades Only)						
V _{DD1} Supply Current	I _{DD1 (10)}					
5 V/3 V Operation			7.1	9.0	mA	5 MHz logic signal frequency
3 V/5 V Operation			3.7	5.4	mA	5 MHz logic signal frequency
V _{DD2} Supply Current	I _{DD2 (10)}					
5 V/3 V Operation			2.2	3.0	mA	5 MHz logic signal frequency
3 V/5 V Operation			4.1	5.0	mA	5 MHz logic signal frequency
90 Mbps (CRWZ Grade Only)						
VDD1 Supply Current	I _{DD1 (90)}					
5 V/3 V Operation			57	82	mA	45 MHz logic signal frequency
3 V/5 V Operation			30	52	mA	45 MHz logic signal frequency

Parameter	Symbol	Min	Тур	Max	Unit	Test Conditions
V _{DD2} Supply Current	I _{DD2 (90)}		.,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	max	•	
5 V/3 V Operation	1002 (90)		18	27	mA	45 MHz logic signal frequency
3 V/5 V Operation			31	43	mA	45 MHz logic signal frequency
ADuM2402 Total Supply Current, Four Channels ²			0.			······································
DC to 2 Mbps						
V _{DD1} Supply Current	IDD1 (Q)					
5 V/3 V Operation	1001 (Q)		1.5	2.1	mA	DC to 1 MHz logic signal frequency
3 V/5 V Operation			0.9	1.5	mA	DC to 1 MHz logic signal frequency
V _{DD2} Supply Current	I _{DD2 (Q)}					
5 V/3 V Operation	1002 (Q)		0.9	1.5	mA	DC to 1 MHz logic signal frequency
3 V/5 V Operation			1.5	2.1	mA	DC to 1 MHz logic signal frequency
10 Mbps (BRWZ and CRWZ Grades Only)						5 5 1 7
V _{DD1} Supply Current	DD1 (10)					
5 V/3 V Operation			5.6	7.0	mA	5 MHz logic signal frequency
3 V/5 V Operation			3.0	4.2	mA	5 MHz logic signal frequency
V _{DD2} Supply Current	DD2 (10)					
5 V/3 V Operation			3.0	4.2	mA	5 MHz logic signal frequency
3 V/5 V Operation			5.6	7.0	mA	5 MHz logic signal frequency
90 Mbps (CRWZ Grade Only)						
VDD1 Supply Current	DD1 (90)					
5 V/3 V Operation			44	62	mA	45 MHz logic signal frequency
3 V/5 V Operation			24	39	mA	45 MHz logic signal frequency
VDD2 Supply Current	I _{DD2 (90)}					
5 V/3 V Operation			24	39	mA	45 MHz logic signal frequency
3 V/5 V Operation			44	62	mA	45 MHz logic signal frequency
For All Models						
Input Currents	I _{IA} , I _{IB} , I _{IC} , I _{ID} , I _{E1} , I _{E2}	-10	+0.01	+10	μA	$\begin{array}{l} 0 \; V \leq V_{\text{IA}}, V_{\text{IB}}, V_{\text{IC}}, V_{\text{ID}} \leq V_{\text{DD1}} \; or \; V_{\text{DD2}}, \\ 0 \; V \leq V_{\text{E1}}, V_{\text{E2}} \leq V_{\text{DD1}} \; or \; V_{\text{DD2}} \end{array} \end{array} \label{eq:VID}$
Logic High Input Threshold	$V_{\text{IH}}, V_{\text{EH}}$					
5 V/3 V Operation		2.0			V	
3 V/5 V Operation		1.6			V	
Logic Low Input Threshold	$V_{\text{IL}}, V_{\text{EL}}$					
5 V/3 V Operation				0.8	V	
3 V/5 V Operation				0.4	V	
Logic High Output Voltages	Voah, Vobh, Voch, Vodh	(V _{DD1} or V _{DD2}) – 0.1	(V _{DD1} or V _{DD2})		V	$I_{\text{Ox}} = -20 \ \mu\text{A}, V_{\text{Ix}} = V_{\text{IxH}}$
		(V _{DD1} or V _{DD2}) – 0.4	(V _{DD1} or V _{DD2}) – 0.2		V	$I_{\text{Ox}} = -4 \text{ mA}, V_{\text{Ix}} = V_{\text{IxH}}$
Logic Low Output Voltages	VOAL, VOBL		0.0	0.1	V	$I_{\text{Ox}} = 20 \ \mu\text{A}, \ V_{\text{Ix}} = V_{\text{IxL}}$
	VOCL, VODL		0.04	0.1	V	$I_{\text{Ox}} = 400 \ \mu\text{A}$, $V_{\text{Ix}} = V_{\text{IxL}}$
			0.2	0.4	V	$I_{Ox} = 4 \text{ mA}, V_{Ix} = V_{IxL}$
SWITCHING SPECIFICATIONS						
ADuM240xARWZ						
Minimum Pulse Width ³	PW			1000	ns	$C_L = 15 \text{ pF}$, CMOS signal levels
Maximum Data Rate ⁴		1			Mbps	$C_L = 15 \text{ pF}$, CMOS signal levels
Propagation Delay ⁵	tPHL, tPLH	50	70	100	ns	$C_L = 15 \text{ pF}$, CMOS signal levels
Pulse-Width Distortion, $ t_{PLH} - t_{PHL} ^5$	PWD			40	ns	$C_L = 15 \text{ pF}$, CMOS signal levels
Propagation Delay Skew ⁶	tрsк			50	ns	$C_L = 15 \text{ pF}$, CMOS signal levels
Channel-to-Channel Matching ⁷	tpskcd/tpskod			50	ns	$C_L = 15 \text{ pF}$, CMOS signal levels
ADuM240xBRWZ	DW/			100		
Minimum Pulse Width ³	PW	10		100	ns	$C_L = 15 \text{ pF}$, CMOS signal levels
Maximum Data Rate ⁴		10	25		Mbps	$C_L = 15 \text{ pF}$, CMOS signal levels
Propagation Delay ⁵	tphl, tplh	15	35	50	ns	$C_L = 15 \text{ pF}$, CMOS signal levels

ParameterSymbolMinTypMaxUnitTest ConditionsPulse Width Distortion, $ t_{Ru} - t_{Ru} ^2$ PWD3nsC, = 15 pF, CMOS signal levelsChange vs. Temperaturet_{vx.}22nsC, = 15 pF, CMOS signal levelsPropagation Delay Skew ⁴ t_{vx.}3nsC, = 15 pF, CMOS signal levelsChannel-to-Channel Matching, Opposing-Directional Channels ⁷ t_{soco}6nsC, = 15 pF, CMOS signal levelsChannel-to-Channel Matching, Opposing-Directional Channels ⁷ t_soco6nsC, = 15 pF, CMOS signal levelsADUM240xCRWZt_soco8.311.1nsC, = 15 pF, CMOS signal levelsMinimum Pulse Width ³ PW8.311.1nsC, = 15 pF, CMOS signal levelsPulse Width Distortion, $ t_{trut} - t_{rel} ^3$ PWD0.52nsC, = 15 pF, CMOS signal levelsPulse Width Distortion, $ t_{trut} - t_{rel} ^3$ PWD0.52nsC, = 15 pF, CMOS signal levelsChannel-to-Channel Matching, Codirectional Channels ⁷ t_t_{vx.}14nsC, = 15 pF, CMOS signal levelsChannel-to-Channel Matching, Output Disable Propagation Delay (High/Low to High Impedance)t_t_{vx.}68nsC, = 15 pF, CMOS signal levelsOutput Disable Propagation Delay (High/Low to High Impedance)t_t_{vx.}68nsC, = 15 pF, CMOS signal levelsOutput Disable Propagation Delay (High/Low to High Impedance)t_t_{vx.}1.1msC, = 15 pF, CMOS signal levels <th></th> <th></th> <th></th> <th></th> <th></th> <th></th> <th>1</th>							1
Change vs. Temperature5ps/°CC. = 15 pF, CMOS signal levelsPropagation Delay Skev ⁴ trsit22nsC. = 15 pF, CMOS signal levelsChannel-to-Channel Matching, Opposing-Directional Channels'trsic3nsC. = 15 pF, CMOS signal levelsChannel-to-Channel Matching, Opposing-Directional Channels'trsico6nsC. = 15 pF, CMOS signal levelsADUA2doxCRWZMinimum Pulse Width ³ PW8.311.1nsC. = 15 pF, CMOS signal levelsMinimum Pulse Width ³ PW8.311.1nsC. = 15 pF, CMOS signal levelsPulse Width Distortion, Itsus - trsiPWD0.52nsC. = 15 pF, CMOS signal levelsPulse Width Distortion, Itsus - trsiPWD0.52nsC. = 15 pF, CMOS signal levelsPropagation Delaytsxic14nsC. = 15 pF, CMOS signal levelsPropagation Delay Skew ⁴ tsxic14nsC. = 15 pF, CMOS signal levelsCodirectional Channels'tsxic2nsC. = 15 pF, CMOS signal levelsChannel-to-Channel Matching, Output Disable Propagation Delaytsxic5nsC. = 15 pF, CMOS signal levelsOutput Rise/Fall Time (10% to 90%) Utput Rise/Fall Time (10% to 90%) Utput Rise/Fall Time (10% to 90%) SW3 Operationtsxic3.0nsc. = 15 pF, CMOS signal levelsSWS Operationcommon-Mode Transient Immunity at Logic Lipi Output ⁴ [CMi]2535kV/µsV _{in} = V ₂₀ or V ₂₀₅ , V ₂₀ = 1000 V, transient magnitude = 800 V <t< th=""><th>Parameter</th><th>Symbol</th><th>Min</th><th>Тур</th><th>Max</th><th>Unit</th><th>Test Conditions</th></t<>	Parameter	Symbol	Min	Тур	Max	Unit	Test Conditions
Propagation Delay Skew ⁶ trsk22nsC = 15 pF, CMOS signal levelsChannel-to-Channel Matching, Opposing-Directional Channels'tsxco3nsC = 15 pF, CMOS signal levelsChannel-to-Channel Matching, Opposing-Directional Channels'tsxco6nsC = 15 pF, CMOS signal levelsADUM240xCRWZ8.311.1nsC = 15 pF, CMOS signal levelsMaximum Data Rate ⁴ 90120MbpsC = 15 pF, CMOS signal levelsPropagation Delay Stmt, text203040nsC = 15 pF, CMOS signal levelsPulse Width Distortion, [t_n + text]203040nsC = 15 pF, CMOS signal levelsPulse Width Distortion, [t_n + text]PWD0.52nsC = 15 pF, CMOS signal levelsPropagation Delay Skew ⁶ tmt,14nsC = 15 pF, CMOS signal levelsChannel-to-Channel Matching, Opposing-Directional Channels'tmt,14nsC = 15 pF, CMOS signal levelsChannel-to-Channel Matching, Output Disable Propagation Delay (High Impedance to HighLow)tmt,tmt,tmt,tmt,Output Bissel-Propagation Delay (High Impedance to HighLow)tmt,tmt,tmt,tmt,tmt,Output Bissel-Propagation Delay (High Impedance to HighLow)tmt,tmt,tmt,tmt,tmt,Output Bissel-Propagation Delay (High Impedance to HighLow)tmt,tmt,tmt,tmt,tmt,S V/3 V Operation 3 V/5 V Operationf.30nscc = 15 pF, CMO	Pulse Width Distortion, $ t_{PLH} - t_{PHL} ^5$	PWD			3	ns	$C_L = 15 \text{ pF}$, CMOS signal levels
Channel-to-Channel Matching, Codirectional Channels'tosco3nsC_ = 15 pF, CMOS signal levelsChannel-to-Channel Matching, Opposing-Directional Channels'tosco6nsC_ = 15 pF, CMOS signal levelsADuM240xCRWZ6nsC_ = 15 pF, CMOS signal levels6nsC_ = 15 pF, CMOS signal levelsMinimum Data Rate*90120MbpsC_ = 15 pF, CMOS signal levels6nsC_ = 15 pF, CMOS signal levelsPropagation Delay*tret, truet203040nsC_ = 15 pF, CMOS signal levelsPropagation Delaystret, truet203040nsC_ = 15 pF, CMOS signal levelsChange vs. Temperatureps/CC_ = 15 pF, CMOS signal levelsps/CC_ = 15 pF, CMOS signal levelsPropagation Delay Skew*trsk14nsC_ = 15 pF, CMOS signal levelsChannel-to-Channel Matching, Output Disable Propagation Delay (High/Low to High Impedance)trsk, truet68nsC_ = 15 pF, CMOS signal levelsOutput Disable Propagation Delay (High/Low to High Impedance)trsk, truet68nsC_ = 15 pF, CMOS signal levelsOutput Disable Propagation Delay (High/Low to High Impedance)trsk, truet68nsC_ = 15 pF, CMOS signal levelsOutput Disable Propagation Delay (High/Low to High Impedance)trsk, truet3.0nsC_ = 15 pF, CMOS signal levelsOutput Disable Propagation Delay (High Impedance)trsk, truet3.0nsC_ = 15 pF, CMOS signal levels <td< td=""><td>Change vs. Temperature</td><td></td><td></td><td>5</td><td></td><td>ps/°C</td><td>$C_L = 15 \text{ pF}$, CMOS signal levels</td></td<>	Change vs. Temperature			5		ps/°C	$C_L = 15 \text{ pF}$, CMOS signal levels
Codirectional Channels' Channel-to-Channel Matching, Opposing-Directional Channels' ADUM240xCRWZtwo6nsC. = 15 pF, CMOS signal levelsMinimum Pulse Width ³ Maximum Data Rate ⁴ Propagation Delay ⁵ PW8.311.1nsC. = 15 pF, CMOS signal levelsPulse Width Distortion, [bar + true] ⁵ Change vs. Temperature Compagation Delay Skew ⁶ true, true203040nsC. = 15 pF, CMOS signal levelsPulse Width Distortion, [bar + true] ⁵ Change vs. TemperaturePWD0.52nsC. = 15 pF, CMOS signal levelsPropagation Delay Skew ⁶ Channel-to-Channel Matching, Codirectional Channels'trax14nsC. = 15 pF, CMOS signal levelsChannel-to-Channel Matching, Opposing-Directional Channels'traxo5nsC. = 15 pF, CMOS signal levelsFor All Modelstrue, true68nsC. = 15 pF, CMOS signal levelsOutput Disable Propagation Delay (High Impedance to High/Low)true, true68nsC. = 15 pF, CMOS signal levelsOutput Rise/Fall Time (10% to 90%)true, true3.0nsC. = 15 pF, CMOS signal levelsC. = 15 pF, CMOS signal levelsCommon-Mode Transient Immunity at Logic Lingh Output ⁴ [CM ₁]2535kV/µsV _{in} = Voin or Voin, Voin = 1000 V, transient magnitude = 800 VS V/3 V Operation S V/3 V Operation[CM ₁]2535kV/µsV _{in} = 0, V _{in} = 1000 V, transient magnitude = 800 VRefresh Rate S V/3 V Operation 3 V/5 V Operation[CM ₁]25 <td< td=""><td>Propagation Delay Skew⁶</td><td>t_{PSK}</td><td></td><td></td><td>22</td><td>ns</td><td>$C_L = 15 \text{ pF}$, CMOS signal levels</td></td<>	Propagation Delay Skew ⁶	t _{PSK}			22	ns	$C_L = 15 \text{ pF}$, CMOS signal levels
Opposing-Directional Channels?NumberNumberNumberADUM240xCRWZPW8.311.1nsCL = 15 pF, CMOS signal levelsMinimum Pulse Width ³ PW90120MbpsCL = 15 pF, CMOS signal levelsPropagation Delay ⁵ tmu, truit203040nsCL = 15 pF, CMOS signal levelsPulse Width Distortion, [truit - truit]PWD0.52nsCL = 15 pF, CMOS signal levelsPropagation Delay ⁵ truit, truit3ps/*CCL = 15 pF, CMOS signal levelsPropagation Delay Skew ⁶ trsx14nsCL = 15 pF, CMOS signal levelsChannel-to-Channel Matching, Opposing-Directional Channels?trsxco2nsCL = 15 pF, CMOS signal levelsChannel-to-Channel Matching, Output Disable Propagation Delay (High Impedance)trsxco5nsCL = 15 pF, CMOS signal levelsOutput Disable Propagation Delay (High Impedance)trszt, truit68nsCL = 15 pF, CMOS signal levelsOutput Rise/Fall Time (10% to 90%) to VDerationtr/t10nsCL = 15 pF, CMOS signal levelsS V/3 V Operation[CMu]2535kV/µsV _{in} = Voor, Voor, Voor, Voor, E = 1000 V, transient magnitude = 800 VCommon-Mode Transient Immunity at Logic Lingh Output*[CMu]2535kV/µsS V/3 V Operation[CMu]2535kV/µsV _{in} = 0V, Voor, Voor, Hou transient magnitude = 800 VCommon-Mode Transient Immunity at Logic Lingh Output*[CMu]0.10 <td>5.</td> <td>tpskcd</td> <td></td> <td></td> <td>3</td> <td>ns</td> <td>$C_L = 15 \text{ pF}$, CMOS signal levels</td>	5.	t pskcd			3	ns	$C_L = 15 \text{ pF}$, CMOS signal levels
Minimum Pulse Width 3 PW8.311.1nsC _z = 15 pF, CMOS signal levelsMaximum Data Rate490120MbpsC _z = 15 pF, CMOS signal levelsPropagation Delay5tent, trun203040nsC _z = 15 pF, CMOS signal levelsPulse Width Distorion, $[t_{VH} - t_{PH}]^5$ PWD3020nsC _z = 15 pF, CMOS signal levelsPropagation Delay Skew6tent3ps/°CC _z = 15 pF, CMOS signal levelsps/°CC _z = 15 pF, CMOS signal levelsChannel-to-Channel Matching, Codirectional Channels7tent2nsC _z = 15 pF, CMOS signal levelsChannel-to-Channel Matching, Opposing-Directional Channels7tent5nsC _z = 15 pF, CMOS signal levelsFor All Modelstent, tent68nsC _z = 15 pF, CMOS signal levelsOutput Disable Propagation Delay (High/Low to High Impedance)tent, tent68nsC _z = 15 pF, CMOS signal levelsOutput Enable Propagation Delay (High/Low to High Impedance)tent, tent68nsC _z = 15 pF, CMOS signal levelsOutput Reserval Time (10% to 90%) S V/3 V Operationtent, tent3.0nsC _z = 15 pF, CMOS signal levelsCommon-Mode Transient Immunity at Logic Low Output*[CM ₁]2535KV/µsV _x = 0 V, v _x = 1000 V, transient magnitude = 800 VCommon-Mode Transient Immunity at Logic Low Output*[CM ₁]2535KV/µsV _x = 0 V, v _x = 1000 V, transient magnitude = 800 VS V/3 V O	5,	t pskod			6	ns	$C_L = 15 \text{ pF}$, CMOS signal levels
Maximum Data Rate490120MbpsCL = 15 pF, CMOS signal levelsPropagation Delay5treat, trut203040nsCL = 15 pF, CMOS signal levelsPulse Width Distortion, $ trut - treat]5PWD0.52nsCL = 15 pF, CMOS signal levelsChange vs. Temperatureps/*C14nsCL = 15 pF, CMOS signal levelsPropagation Delay Skew6trest14nsCL = 15 pF, CMOS signal levelsChannel-to-Channel Matching,Codirectional Channels7trest2nsCL = 15 pF, CMOS signal levelsChannel-to-Channel Matching,Opposing-Directional Channels7trest2nsCL = 15 pF, CMOS signal levelsFor All Modelstresttrest5nsCL = 15 pF, CMOS signal levelsOutput Disable Propagation Delay(High/Low to High Impedance)trest, trut68nsCL = 15 pF, CMOS signal levelsOutput Rise/Fall Time (10% to 90%)to Output Rise/Fall Time (10% to 90%)tr/tr3.0nsNsCL = 15 pF, CMOS signal levelsS V/3 V Operation[CM_i]2535KV/µsVin = Vooi or Vooz, Vom = 1000 V,transient magnitude = 800 VRefresh RateS V/3 V Operationfr1.2MbpsNsVin = 0.0, Vin = 0.0, Vin$	ADuM240xCRWZ						
Propagation Delaystmt, trut203040nsC. = 15 pF, CMOS signal levelsPulse Width Distortion, [trut - tmt]sPWD0.52nsC. = 15 pF, CMOS signal levelsChange vs. Temperature314nsC. = 15 pF, CMOS signal levelsPropagation Delay Skew ⁶ trsk14nsC. = 15 pF, CMOS signal levelsChannel-to-Channel Matching, Codirectional Channels?trsk2nsC. = 15 pF, CMOS signal levelsChannel-to-Channel Matching, Opposing-Directional Channels?trskop5nsC. = 15 pF, CMOS signal levelsFor All Modelstrsktrskop5nsC. = 15 pF, CMOS signal levelsOutput Disable Propagation Delay (High Impedance)trsky, trgz,68nsC. = 15 pF, CMOS signal levelsOutput Rise/Fall Time (10% to 90%) Uutput Rise/Fall Time (10% to 90%)trgk, trgz,68nsC. = 15 pF, CMOS signal levelsCommon-Mode Transient Immunity at Logic High Output ⁸ [CMt]2535kV/µsV _n = Voor or Voos, Von = 1000 V, transient magnitude = 800 VRefresh Rate S V/3 V Operationfr1.2MbpsNbpsInsient magnitude = 800 VNo (D)trgfor (D)0.19mA/MbpsN/MbpsN/S V Operation 3 V/S V Operation1.00 (D)0.19mA/MbpsS V/3 V Operation 3 V/S V Operation1.00 (D)0.03mA/Mbps	Minimum Pulse Width ³	PW		8.3	11.1	ns	$C_{L} = 15 \text{ pF}$, CMOS signal levels
Pulse Width Distortion, teu+ - teu SPWD0.52nsCL = 15 pF, CMOS signal levelsChange vs. Temperature3ps/°CCL = 15 pF, CMOS signal levelsps/°CCL = 15 pF, CMOS signal levelsPropagation Delay Skew ⁶ trsx14nsCL = 15 pF, CMOS signal levelsChannel-to-Channel Matching, Codirectional Channels?trsx2nsCL = 15 pF, CMOS signal levelsChannel-to-Channel Matching, Opposing-Directional Channels?trsxop5nsCL = 15 pF, CMOS signal levelsFor All Modelstrsxop5nsCL = 15 pF, CMOS signal levelsOutput Disable Propagation Delay (High Impedance)trsv, trut68nsCL = 15 pF, CMOS signal levelsOutput Rise/Fall Time (10% to 90%) to VS V Operationtrsv, trut68nsCL = 15 pF, CMOS signal levelsCommon-Mode Transient Immunity at Logic Low Output*[CMt]2535kV/µsVs = Voot or Voot, Vom = 1000 V, transient magnitude = 800 VRefresh Rate S V/3 V Operationf,1.1MbpsVs = Voot or Voot, Vom = 1000 V, transient magnitude = 800 VRefresh Rate S V/3 V Operationf,1.2MbpsNdpsN/S V Operation0.10mA/MbpsS V/3 V Operation0.10mA/Mbps	Maximum Data Rate ⁴		90	120		Mbps	C _L = 15 pF, CMOS signal levels
Change vs. Temperature3 $ps/^{PC}$ $C_{L} = 15 pF, CMOS signal levelsPropagation Delay Skew6tesk14nsC_{L} = 15 pF, CMOS signal levelsChannel-to-Channel Matching,Codirectional Channels7teskco2nsC_{L} = 15 pF, CMOS signal levelsChannel-to-Channel Matching,Opposing-Directional Channels7teskco5nsC_{L} = 15 pF, CMOS signal levelsFor All Models5nsC_{L} = 15 pF, CMOS signal levelsC_{L} = 15 pF, CMOS signal levelsOutput Disable Propagation Delay(High/Low to High Impedance)tesk.68nsC_{L} = 15 pF, CMOS signal levelsOutput Enable Propagation Delay(High/Low to High Impedance)tesk.tesk.3.0nsC_{L} = 15 pF, CMOS signal levelsOutput Bise/Fall Time (10% to 90%)to/trtesk.tesk.3.0nsC_{L} = 15 pF, CMOS signal levelsS V/3 V Operationtesk.3.0nsC_{L} = 15 pF, CMOS signal levelsC_{L} = 15 pF, CMOS signal levelsCommon-Mode Transient Immunity atLogic Ling Output8[CM_{eff}]2535kV/µsV_{ix} = V_{DDi} or V_{DD2}, V_{CAI} = 1000 V,transient magnitude = 800 VRefersh RateS V/3 V Operationfr1.2Mbpsiransient magnitude = 800 VN/S V Operation1.1Mbpsiransient magnitude = 800 Viransient magnitude = 800 VN/S V Operation0.19mA/Mbpsiransient magnitude = 800 VS V/3 V Operation0.19mA/MbpsOutput Dynamic Supply Current per Channel9$	Propagation Delay ⁵	tphl, tplh	20	30	40	ns	$C_{L} = 15 \text{ pF}$, CMOS signal levels
Change vs. Temperature3 $ps/^{PC}$ $C_{L} = 15 pF, CMOS signal levelsPropagation Delay Skew6tesk14nsC_{L} = 15 pF, CMOS signal levelsChannel-to-Channel Matching,Codirectional Channels7teskco2nsC_{L} = 15 pF, CMOS signal levelsChannel-to-Channel Matching,Opposing-Directional Channels7teskco5nsC_{L} = 15 pF, CMOS signal levelsFor All Models5nsC_{L} = 15 pF, CMOS signal levelsC_{L} = 15 pF, CMOS signal levelsOutput Disable Propagation Delay(High/Low to High Impedance)tesk.68nsC_{L} = 15 pF, CMOS signal levelsOutput Enable Propagation Delay(High/Low to High Impedance)tesk.tesk.3.0nsC_{L} = 15 pF, CMOS signal levelsOutput Bise/Fall Time (10% to 90%)to/trtesk.tesk.3.0nsC_{L} = 15 pF, CMOS signal levelsS V/3 V Operationtesk.3.0nsC_{L} = 15 pF, CMOS signal levelsC_{L} = 15 pF, CMOS signal levelsCommon-Mode Transient Immunity atLogic Ling Output8[CM_{eff}]2535kV/µsV_{ix} = V_{DDi} or V_{DD2}, V_{CAI} = 1000 V,transient magnitude = 800 VRefersh RateS V/3 V Operationfr1.2Mbpsiransient magnitude = 800 VN/S V Operation1.1Mbpsiransient magnitude = 800 Viransient magnitude = 800 VN/S V Operation0.19mA/Mbpsiransient magnitude = 800 VS V/3 V Operation0.19mA/MbpsOutput Dynamic Supply Current per Channel9$	Pulse Width Distortion, $ t_{PLH} - t_{PHL} ^5$	PWD		0.5	2	ns	$C_{L} = 15 \text{ pF}$, CMOS signal levels
Propagation Delay Skew ⁶ tesk14ns $C_{L} = 15 \text{ pF}$, CMOS signal levelsChannel-to-Channel Matching, Codirectional Channels?teskco2ns $C_{L} = 15 \text{ pF}$, CMOS signal levelsChannel-to-Channel Matching, Opposing-Directional Channels?teskco5ns $C_{L} = 15 \text{ pF}$, CMOS signal levelsFor All Modelsteskco5ns $C_{L} = 15 \text{ pF}$, CMOS signal levelsOutput Disable Propagation Delay (High/Low to High Impedance)teskco68ns $C_{L} = 15 \text{ pF}$, CMOS signal levelsOutput Enable Propagation Delay (High/Low to High Impedance)teskco5ns $C_{L} = 15 \text{ pF}$, CMOS signal levelsOutput Rise/Fall Time (10% to 90%)te/tr3.0ns $C_{L} = 15 \text{ pF}$, CMOS signal levelsS V/3 V Operation3.0ns1.1 $S_{L} = 15 \text{ pF}$, CMOS signal levelsCommon-Mode Transient Immunity at Logic Ligh Output ⁸ [CML]2535kV/µs $V_{h} = V_{DD1}$ or V_{DD2} , $V_{cm} = 1000 V$, transient magnitude = 800 VRefresh Rate S V/3 V Operationf,1.2MbpsNbpsInput Dynamic Supply Current per Channel ⁹ $D_{DD1(D)$ 0.19mA/MbpsS V/3 V Operation0.19mA/MbpsmA/MbpsS V/3 V Operation0.03mA/Mbps	· · · ·			3		ps/°C	
Channel-to-Channel Matching, Codirectional Channels'tesco2ns $C_{L} = 15 \text{ pF}$, CMOS signal levelsChannel-to-Channel Matching, Opposing-Directional Channels'tesco5ns $C_{L} = 15 \text{ pF}$, CMOS signal levelsFor All ModelsDutput Disable Propagation Delay (High/Low to High Impedance)tesco68ns $C_{L} = 15 \text{ pF}$, CMOS signal levelsOutput Enable Propagation Delay (High/Low to High Impedance)test, test68ns $C_{L} = 15 \text{ pF}$, CMOS signal levelsOutput Enable Propagation Delay (High Impedance to High/Low)test, test68ns $C_{L} = 15 \text{ pF}$, CMOS signal levelsOutput Rise/Fall Time (10% to 90%)te/tr3.0ns $C_{L} = 15 \text{ pF}$, CMOS signal levelsS V/3 V Operation1/23.0ns $C_{L} = 15 \text{ pF}$, CMOS signal levelsCommon-Mode Transient Immunity at Logic Low Output ⁸ $ CM_{H} $ 2535 $kV/\mu s$ $V_{h} = V_{DO1} \text{ or }V_{DD2}, V_{CM} = 1000 V,transient magnitude = 800 VRefresh Rate5 V/3 V Operationfr1.2MbpsW_{h} = 0 \text{ V}, V_{cM} = 1000 \text{ V},transient magnitude = 800 VS V/5 V Operation1.1Mbps1.1MbpsInput Dynamic Supply Current per Channel?D_{O1(D)D_{O1(D)}D_{A}/MbpsS V/3 V OperationD_{O1(D)D_{O1(D)}D_{A}/MbpsS V/3 V OperationD_{O1(D)}D_{O1(D)}D_{A}/MbpsS V/3 V OperationD_{O1(D)}D_{O1(D)}D_{A}/Mbps$	U .	t _{PSK}			14	ns	$C_{L} = 15 \text{ pF}$, CMOS signal levels
Opposing-Directional Channels7InitialFor All ModelsOutput Disable Propagation Delay (High/Low to High Impedance) t_{HEZ} , t_{FZL} 68ns $C_L = 15 \text{ pF}$, CMOS signal levelsOutput Enable Propagation Delay (High Impedance) t_{FZL} , t_{FZL} 68ns $C_L = 15 \text{ pF}$, CMOS signal levelsOutput Enable Propagation Delay (High Impedance) t_{FZL} , t_{FZL} 68ns $C_L = 15 \text{ pF}$, CMOS signal levelsOutput Rise/Fall Time (10% to 90%) 5 V/3 V Operation t_{Z}/t_{T} 3.0ns $C_L = 15 \text{ pF}$, CMOS signal levelsCommon-Mode Transient Immunity at Logic Low Output8[CMH]2535 $kV/\mu s$ $V_{k} = V_{DD1}$ or V_{DD2} , $V_{CM} = 1000 V$, transient magnitude = 800 VRefresh Rate 5 V/3 V Operationfr1.2MbpsN/5 V Operation1.1MbpsNo V5 V Operation0.19mA/MbpsS V/3 V Operation0.10mA/Mbps	Channel-to-Channel Matching,	t _{PSKCD}			2	ns	$C_L = 15 \text{ pF}$, CMOS signal levels
For All Modelstotal		t _{PSKOD}			5	ns	$C_L = 15 \text{ pF}$, CMOS signal levels
(High/Low to High Impedance)Impedance <td></td> <td></td> <td></td> <td></td> <td></td> <td></td> <td></td>							
$ \begin{array}{c c c c c c c c } Output Enable Propagation Delay (High Impedance to High/Low) & t_{P2H}, t_{P2L} & 6 & 8 & ns & C_L = 15 \ pF, CMOS \ signal \ levels \\ C_L = 15 \ pF, CMOS \ levels \\ C_L = 15 \ pF, CMOS \ levels \\ C_L = 15 \ pF, CMOS \ levels \\ C_L = 15 \ pF, CMOS \ levels \\ C_L = 15 \ pF, CMOS \ levels \\ C_L = 15 \ pF, CMOS \ levels \\ C_L = 1000 \ V, \ leve$		tphz, tplh		6	8	ns	$C_L = 15 \text{ pF}$, CMOS signal levels
Output Rise/Fall Time (10% to 90%)tr\tr3.0nsC_L = 15 pF, CMOS signal levels5 V/3 V Operation3.0nsnsnsns3 V/5 V Operation2.5nsV/µsV_Ix = V_{DD1} or V_{DD2,} V_{CM} = 1000 V, transient magnitude = 800 VCommon-Mode Transient Immunity at Logic Low Output8[CML]2535kV/µsV_Ix = 0 V, V_{CM} = 1000 V, transient magnitude = 800 VRefresh Ratefr1.2MbpsNsNsNsNs3 V/5 V Operation1.2MbpsNsNsNsNs1 Nput Dynamic Supply Current per Channel?IDDI (D)0.19mA/MbpsNs/Mbps0 Utput Dynamic Supply Current per Channel?IDDI (D)0.03mA/MbpsNs/Mbps	Output Enable Propagation Delay	$t_{\text{PZH}}, t_{\text{PZL}}$		6	8	ns	$C_L = 15 \text{ pF}$, CMOS signal levels
3 V/5 V Operation2.5nsCommon-Mode Transient Immunity at Logic High Output8ICMH2535kV/µsVIx = V_DD1 or V_DD2, V_CM = 1000 V, transient magnitude = 800 VCommon-Mode Transient Immunity at Logic Low Output8ICML2535kV/µsVIx = 0 V, V_{CM} = 1000 V, transient magnitude = 800 VRefresh Rate 5 V/3 V Operation 3 V/5 V Operation 3 V/5 V Operationfr.1.2MbpsInput Dynamic Supply Current per Channel9 5 V/3 V OperationIDDI (D)0.19mA/MbpsOutput Dynamic Supply Current per Channel9 5 V/3 V OperationIDDI (D)0.03mA/Mbps		t _R /t _f					C _L = 15 pF, CMOS signal levels
Common-Mode Transient Immunity at Logic High Output8 $ CM_H $ 2535 $kV/\mu s$ $V_{lx} = V_{DD1}$ or V_{DD2} , $V_{CM} = 1000 V$, transient magnitude = 800 VCommon-Mode Transient Immunity at Logic Low Output8 $ CM_L $ 2535 $kV/\mu s$ $V_{lx} = 0 V$, $V_{CM} = 1000 V$, transient magnitude = 800 VRefresh Rate 5 V/3 V Operation 3 V/5 V Operation 3 V/5 V Operation f_r 1.2MbpsInput Dynamic Supply Current per Channel9 5 V/3 V Operation $I_{DDI (D)$ 0.19mA/MbpsOutput Dynamic Supply Current per Channel9 $I_{DDO (D)}$ 0.03mA/Mbps	5 V/3 V Operation			3.0		ns	
Logic High Output ⁸ ICML2535transient magnitude = 800 VCommon-Mode Transient Immunity at Logic Low Output ⁸ ICML2535kV/µsVIx = 0 V, V _{CM} = 1000 V, transient magnitude = 800 VRefresh Ratefr1.2Mbps5 V/3 V Operation1.1Mbps3 V/5 V Operation1.1Mbps5 V/3 V Operation0.19mA/Mbps5 V/3 V Operation0.10mA/Mbps5 V/3 V Operation0.10mA/Mbps5 V/3 V Operation0.03mA/Mbps	3 V/5 V Operation			2.5		ns	
Logic Low Output8rtransient magnitude = 800 VRefresh Ratefr1.2Mbps5 V/3 V Operation1.2Mbps3 V/5 V Operation1.1MbpsInput Dynamic Supply Current per Channel9IDDI (D)0.195 V/3 V Operation0.10mA/Mbps3 V/5 V Operation0.10mA/Mbps5 V/3 V Operation0.10mA/Mbps5 V/3 V Operation0.00mA/Mbps5 V/3 V Operation0.00mA/Mbps		CM _H	25	35		kV/μs	
5 V/3 V Operation1.2Mbps3 V/5 V Operation1.1MbpsInput Dynamic Supply Current per Channel9Input Dynamic Supply Current per Channel90.193 V/5 V Operation0.10mA/Mbps3 V/5 V Operation0.10mA/Mbps5 V/3 V Operation0.00mA/Mbps5 V/3 V Operation0.00mA/Mbps		CM _L	25	35		kV/μs	
3 V/5 V Operation1MbpsInput Dynamic Supply Current per Channel9IDDI (D)1.1Mbps5 V/3 V Operation0.19mA/Mbps3 V/5 V Operation0.10mA/MbpsOutput Dynamic Supply Current per Channel9IDDO (D)0.035 V/3 V Operation0.03mA/Mbps	Refresh Rate	fr					_
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5 V/3 V Operation 0.19 mA/Mbps 3 V/5 V Operation 0.10 mA/Mbps Output Dynamic Supply Current per Channel ⁹ IDDO (D) nA/Mbps 5 V/3 V Operation 0.03 mA/Mbps	3 V/5 V Operation			1.1		Mbps	
3 V/5 V Operation 0.10 mA/Mbps Output Dynamic Supply Current per Channel ⁹ I _{DDO (D)} 0.03 mA/Mbps	Input Dynamic Supply Current per Channel ⁹	I _{DDI (D)}					
Output Dynamic Supply Current per Channel ⁹ I _{DDO (D)} I 5 V/3 V Operation 0.03 mA/Mbps	5 V/3 V Operation			0.19		mA/Mbps	
5 V/3 V Operation 0.03 mA/Mbps	3 V/5 V Operation			0.10		mA/Mbps	
	Output Dynamic Supply Current per Channel ⁹	I _{DDO (D)}					
3 V/5 V Operation 0.05 mA/Mbps	5 V/3 V Operation			0.03		mA/Mbps	
	3 V/5 V Operation			0.05		mA/Mbps	

¹ All voltages are relative to their respective ground.

² Supply current values are for all four channels combined running at identical data rates. Output supply current values are specified with no output load present. The supply current associated with an individual channel operating at a given data rate can be calculated as described in the Power Consumption section. See Figure 8 through Figure 10 for information on per channel supply current as a function of data rate for unloaded and loaded conditions. See Figure 11 through Figure 15 for total V_{DD1} and V_{DD2} supply currents as a function of data rate for ADuM2400/ADuM2401/ADuM2402 channel configurations.

³ The minimum pulse width is the shortest pulse width at which the specified pulse width distortion is guaranteed.

⁴ The maximum data rate is the fastest data rate at which the specified pulse width distortion is guaranteed.

⁵ t_{PHL} propagation delay is measured from the 50% level of the falling edge of the V_{Ix} signal to the 50% level of the falling edge of the V_{ox} signal. t_{PLH} propagation delay is measured from the 50% level of the rising edge of the V_{ix} signal to the 50% level of the rising edge of the V_{ox} signal.

⁶ t_{PSK} is the magnitude of the worst-case difference in t_{PHL} or t_{PLH} that is measured between units at the same operating temperature, supply voltages, and output load within the recommended operating conditions.

⁷ Codirectional channel-to-channel matching is the absolute value of the difference in propagation delays between any two channels with inputs on the same side of the isolation barrier. Opposing directional channel-to-channel matching is the absolute value of the difference in propagation delays between any two channels with inputs on opposing sides of the isolation barrier.

 8 CM_H is the maximum common-mode voltage slew rate that can be sustained while maintaining V₀ > 0.8V_{DD2}. CM_L is the maximum common-mode voltage slew rate that can be sustained while maintaining V₀ < 0.8 V. The common-mode voltage slew rates apply to both rising and falling common-mode voltage edges. The transient magnitude is the range over which the common mode is slewed.

⁹ Dynamic supply current is the incremental amount of supply current required for a 1 Mbps increase in signal data rate. See Figure 8 through Figure 10 for information on per channel supply current for unloaded and loaded conditions. See the Power Consumption section for guidance on calculating per channel supply current for a given data rate.

PACKAGE CHARACTERISTICS

Table 4.

Parameter	Symbol	Min	Тур	Max	Unit	Test Conditions
Resistance (Input to Output) ¹	R _{I-O}		10 ¹²		Ω	
Capacitance (Input to Output) ¹	CI-O		2.2		pF	f = 1 MHz
Input Capacitance ²	Cı		4.0		pF	
IC Junction-to-Case Thermal Resistance, Side 1			33		°C/W	Thermocouple located at center
IC Junction-to-Case Thermal Resistance, Side 2 θ _{Jco}			28		°C/W	of package underside

¹ Device considered a two-terminal device: Pin 1, Pin 2, Pin 3, Pin 4, Pin 5, Pin 6, Pin 7, and Pin 8 shorted together and Pin 9, Pin 10, Pin 11, Pin 12, Pin 13, Pin 14, Pin 15, and Pin 16 shorted together.

² Input capacitance is from any input data pin to ground.

REGULATORY INFORMATION

The ADuM240x are approved by the organizations listed in Table 5. Refer to Table 10 and the Insulation Lifetime section for details regarding recommended maximum working voltages for specific cross-isolation waveforms and insulation levels.

Table 5.

UL	CSA	VDE
Recognized under 1577 component recognition program ¹	Approved under CSA Component Acceptance Notice #5A	Certified according to DIN V VDE V 0884-10 (VDE V 0884-10):2006-12 ²
Double/reinforced insulation, 5000 V rms isolation voltage	Reinforced insulation per CSA 60950-1-03 and IEC 60950-1, 600 V rms (848 V peak) maximum working voltage Reinforced insulation per IEC 60601-1 250 V rms (353 V peak) maximum working voltage	Reinforced insulation, 846 V peak
File E214100	File 205078	File 2471900-4880-0001

¹ In accordance with UL 1577, each ADuM240x is proof tested by applying an insulation test voltage \geq 6000 V rms for 1 second (current leakage detection limit = 10 µA). ² In accordance with DIN V VDE V 0884-10, each ADuM240x is proof tested by applying an insulation test voltage \geq 1590 V peak for 1 second (partial discharge detection limit = 5 pC). The * marking branded on the component designates DIN V VDE V 0884-10 approval.

INSULATION AND SAFETY-RELATED SPECIFICATIONS

Table 6. Conditions Parameter Value Unit Symbol 5000 **Rated Dielectric Insulation Voltage** V rms 1-minute duration Minimum External Air Gap (Clearance) L(I01) >8.0 Measured from input terminals to output terminals, mm shortest line of sight distance through air Minimum External Tracking (Creepage) L(I02) >8.0 Measured from input terminals to output terminals, mm shortest distance path along body Minimum Internal Gap (Internal Clearance) 0.017 min mm Insulation distance through insulation Tracking Resistance (Comparative Tracking Index) CTI >175 DIN IEC 112/VDE 0303 Part 1 V Isolation Group Illa Material Group (DIN VDE 0110, 1/89, Table 1)

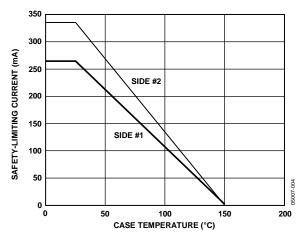
DIN V VDE V 0884-10 (VDE V 0884-10) INSULATION CHARACTERISTICS

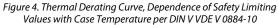
These isolators are suitable for reinforced electrical isolation only within the safety limit data. Maintenance of the safety data is ensured by means of protective circuits.

Note that the * marking on packages denotes DIN V VDE V 0884-10 approval for 846 V peak working voltage.

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Description	Conditions	Symbol	Characteristic	Unit
Installation Classification per DIN VDE 0110				
For Rated Mains Voltage ≤ 300 V rms			l to IV	
For Rated Mains Voltage ≤ 450 V rms			l to ll	
For Rated Mains Voltage ≤ 600 V rms			l to ll	
Climatic Classification			40/105/21	
Pollution Degree (DIN VDE 0110, Table 1)			2	
Maximum Working Insulation Voltage		VIORM	846	V peak
Input-to-Output Test Voltage, Method b1	$V_{IORM} \times 1.875 = V_{PR}$, 100% production test, $t_m = 1$ sec, partial discharge < 5 pC	V _{PR}	1590	V peak
Input-to-Output Test Voltage, Method a		V _{PR}		
After Environmental Tests Subgroup 1	$V_{IORM} \times 1.6 = V_{PR}$, $t_m = 60$ sec, partial discharge < 5 pC		1375	V peak
After Input and/or Safety Test Subgroup 2 and Subgroup 3	$V_{\text{IORM}} \times 1.2 = V_{\text{PR}}, t_{\text{m}} = 60$ sec, partial discharge $< 5 \text{ pC}$		1018	V peak
Highest Allowable Overvoltage	Transient overvoltage, $t_{TR} = 10$ seconds	VTR	6000	V peak
Safety-Limiting Values	Maximum value allowed in the event of a failure; see Figure 4			
Case Temperature		Ts	150	°C
Side 1 Current		I _{S1}	265	mA
Side 2 Current		I _{S2}	335	mA
Insulation Resistance at Ts	$V_{IO} = 500 V$	Rs	>109	Ω





RECOMMENDED OPERATING CONDITIONS

Table 8.

Parameter	Rating
Operating Temperature (T _A)	-40°C to +105°C
Supply Voltages ¹ (V _{DD1} , V _{DD2})	2.7 V to 5.5 V
Input Signal Rise and Fall Times	1.0 ms

¹ All voltages are relative to their respective ground. See the DC Correctness and Magnetic Field Immunity section for information on immunity to external magnetic fields.

ABSOLUTE MAXIMUM RATINGS

Table 9.

Parameter	Rating
Storage Temperature Range (T _{ST})	–65°C to +150°C
Ambient Operating Temperature Range (T _A)	−40°C to +105°C
Supply Voltage Range (V _{DD1} , V _{DD2}) ¹	–0.5 V to +7.0 V
Input Voltage Range (V _{IA} , V _{IB} , V _{IC} , V _{ID} , V _{E1} , V _{E2}) ^{1, 2}	$-0.5V$ to $V_{\text{DDI}}+0.5V$
Output Voltage Range (V _{OA} , V _{OB} , V _{OC} , V _{OD}) ^{1, 2}	-0.5 V to V _{DDO} + 0.5 V
Average Output Current Per Pin ³	
Side 1 (I ₀₁)	–18 mA to +18 mA
Side 2 (I _{O2})	–22 mA to +22 mA
Common-Mode Transients ⁴	–100 kV/µs to +100 kV/µs

¹ All voltages are relative to their respective ground.

 2 V_{\rm DDI} and V_{\rm DDO} refer to the supply voltages on the input and output sides of a given channel, respectively. See the PC Board Layout section.

³ See Figure 4 for maximum rated current values for various temperatures.

⁴ Refers to common-mode transients across the insulation barrier. Commonmode transients exceeding the Absolute Maximum Rating can cause latchup or permanent damage.

Table 10. Maximum Continuous Working Voltage¹

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ESD CAUTION



ESD (electrostatic discharge) sensitive device. Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

Table 10. Maximum Continuous Working Voltage				
Parameter	Max	Unit	Constraint	
AC Voltage, Bipolar Waveform	565	V peak	50-year minimum lifetime	
AC Voltage, Unipolar Waveform				
Reinforced Insulation	846	V peak	Maximum approved working voltage per IEC 60950-1 and VDE V 0884-10	
DC Voltage				
Reinforced Insulation	846	V peak	Maximum approved working voltage per IEC 60950-1 and VDE V 0884-10	
			•	

¹ Refers to continuous voltage magnitude imposed across the isolation barrier. See the Insulation Lifetime section for more details.

Table 11. Truth Table (Positive Logic)

V _{ix} Input ¹	V _{Ex} Input	V _{DDI} State ¹	V _{DDO} State ¹	Vox Output ¹	Notes
Н	H or NC	Powered	Powered	Н	
L	H or NC	Powered	Powered	L	
Х	L	Powered	Powered	Z	
Х	H or NC	Unpowered	Powered	н	Outputs return to input state within 1 μ s of V _{DDI} power restoration.
Х	L	Unpowered	Powered	Z	
Х	x	Powered	Unpowered	Indeterminate	Outputs return to input state within 1 μ s of V _{DDO} power restoration if V _{Ex} state is H or NC. Outputs return to high impedance state within 8 ns of V _{DDO} power restoration if V _{Ex} state is L.

¹ V_{ix} and V_{Ox} refer to the input and output signals of a given channel (A, B, C, or D). V_{Ex} refers to the output enable signal on the same side as the V_{Ox} outputs. V_{DDI} and V_{DDO} refer to the supply voltages on the input and output sides of the given channel, respectively.

PIN CONFIGURATIONS AND FUNCTION DESCRIPTIONS

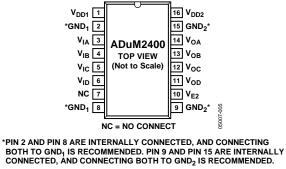
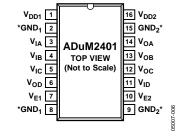


Figure 5. ADuM2400 Pin Configuration

Table 12. ADuM2400 Pin Function Descriptions

Pin No.	Mnemonic	Description
1	V _{DD1}	Supply Voltage for Isolator Side 1, 2.7 V to 5.5 V.
2	GND1	Ground 1. Ground reference for Isolator Side 1.
3	VIA	Logic Input A.
4	VIB	Logic Input B.
5	VIC	Logic Input C.
6	VID	Logic Input D.
7	NC	No Connect.
8	GND ₁	Ground 1. Ground reference for Isolator Side 1.
9	GND ₂	Ground 2. Ground reference for Isolator Side 2.
10	V _{E2}	Output Enable 2. Active high logic input. V _{OA} , V _{OB} , V _{OC} , and V _{OD} outputs are enabled when V _{E2} is high or disconnected. V _{OA} , V _{OB} , V _{OC} , and V _{OD} outputs are disabled when V _{E2} is low. In noisy environments, connecting V _{E2} to an external logic high or low is recommended.
11	Vod	Logic Output D.
12	Voc	Logic Output C.
13	V _{OB}	Logic Output B.
14	Voa	Logic Output A.
15	GND ₂	Ground 2. Ground reference for Isolator Side 2.
16	V _{DD2}	Supply Voltage for Isolator Side 2, 2.7 V to 5.5 V.



*PIN 2 AND PIN 8 ARE INTERNALLY CONNECTED, AND CONNECTING BOTH TO ${\rm GND}_1$ IS RECOMMENDED. PIN 9 AND PIN 15 ARE INTERNALLY CONNECTED, AND CONNECTING BOTH TO ${\rm GND}_2$ IS RECOMMENDED.

Figure 6	ADuM2401	Pin	Configuration
riguic 0.	/1Dum2 101		configuration

Table 13. ADuM2401 Pin Function Descriptions

Pin No.	Mnemonic	Description
1	V _{DD1}	Supply Voltage for Isolator Side 1, 2.7 V to 5.5 V.
2	GND1	Ground 1. Ground reference for Isolator Side 1.
3	VIA	Logic Input A.
4	VIB	Logic Input B.
5	VIC	Logic Input C.
6	Vod	Logic Output D.
7	V _{E1}	Output Enable 1. Active high logic input. V_{OD} output is enabled when V_{E1} is high or disconnected. V_{OD} is disabled when V_{E1} is low. In noisy environments, connecting V_{E1} to an external logic high or low is recommended.
8	GND₁	Ground 1. Ground reference for Isolator Side 1.
9	GND ₂	Ground 2. Ground reference for Isolator Side 2.
10	V _{E2}	Output Enable 2. Active high logic input. V_{OA} , V_{OB} , and V_{OC} outputs are enabled when V_{E2} is high or disconnected. V_{OA} , V_{OB} , and V_{OC} outputs are disabled when V_{E2} is low. In noisy environments, connecting V_{E2} to an external logic high or low is recommended.
11	VID	Logic Input D.
12	Voc	Logic Output C.
13	V _{OB}	Logic Output B.
14	V _{OA}	Logic Output A.
15	GND ₂	Ground 2. Ground reference for Isolator Side 2.
16	V _{DD2}	Supply Voltage for Isolator Side 2, 2.7 V to 5.5 V.

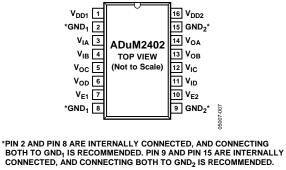
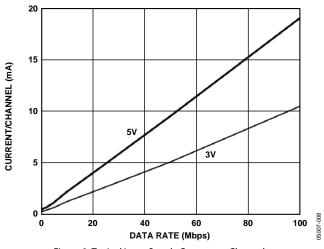


Figure 7. ADuM2402 Pin Configuration

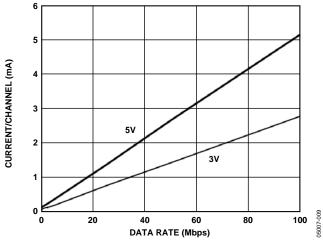
Table 14. ADuM2402 Pin Function Descriptions

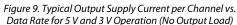
Pin No.	Mnemonic	Description					
1	V _{DD1}	Supply Voltage for Isolator Side 1, 2.7 V to 5.5 V.					
2	GND1	Ground 1. Ground reference for Isolator Side 1.					
3	VIA	Logic Input A.					
4	VIB	Logic Input B.					
5	Voc	Logic Output C.					
6	Vod	Logic Output D.					
7	V _{E1}	Output Enable 1. Active high logic input. V_{OC} and V_{OD} outputs are enabled when V_{E1} is high or disconnected. V_{OC} and V_{OD} outputs are disabled when V_{E1} is low. In noisy environments, connecting V_{E1} to an external logic high or low is recommended.					
8	GND1	Ground 1. Ground reference for Isolator Side 1.					
9	GND ₂	Ground 2. Ground reference for Isolator Side 2.					
10	V _{E2}	Output Enable 2. Active high logic input. V_{OA} and V_{OB} outputs are enabled when V_{E2} is high or disconnected. V_{OA} and V_{OB} outputs are disabled when V_{E2} is low. In noisy environments, connecting V_{E2} to an external logic high or low is recommended.					
11	VID	Logic Input D.					
12	V _{IC}	Logic Input C.					
13	Vob	Logic Output B.					
14	V _{OA}	Logic Output A.					
15	GND ₂	Ground 2. Ground reference for Isolator Side 2.					
16	V _{DD2}	Supply Voltage for Isolator Side 2, 2.7 V to 5.5 V.					

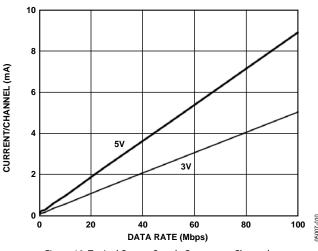
TYPICAL PERFORMANCE CHARACTERISTICS

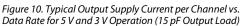


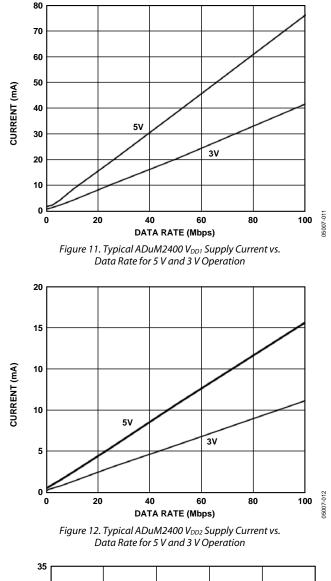


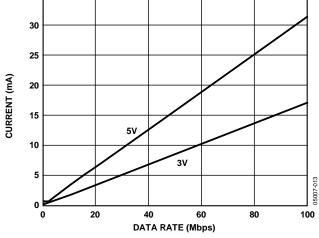


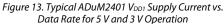












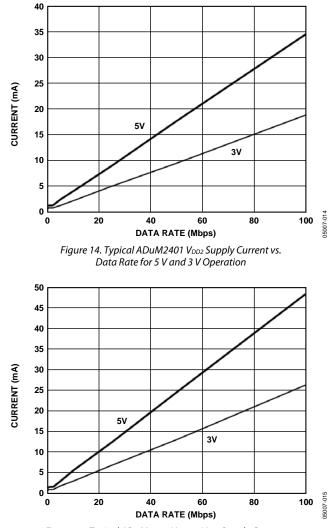
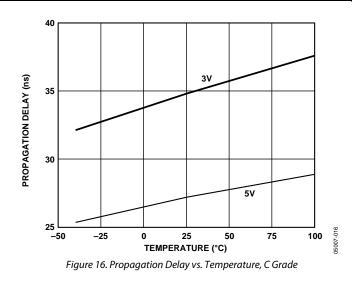


Figure 15. Typical ADuM2402 V_{DD1} or V_{DD2} Supply Current vs. Data Rate for 5 V and 3 V Operation



APPLICATION INFORMATION PC BOARD LAYOUT

The ADuM240x digital isolator requires no external interface circuitry for the logic interfaces. Power supply bypassing is strongly recommended at the input and output supply pins (see Figure 17). Bypass capacitors are most conveniently connected between Pin 1 and Pin 2 for V_{DD1} and between Pin 15 and Pin 16 for V_{DD2} . The capacitor value should be between 0.01 µF and 0.1 µF. The total lead length between both ends of the capacitor and the input power supply pin should not exceed 20 mm. Bypassing between Pin 1 and Pin 8 and between Pin 9 and Pin 16 should be considered unless the ground pair on each package side are connected close to the package.

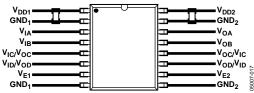
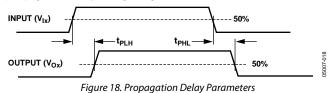


Figure 17. Recommended Printed Circuit Board Layout

In applications involving high common-mode transients, ensure that board coupling across the isolation barrier is minimized. Furthermore, the board layout should be designed such that any coupling that does occur equally affects all pins on a given component side. Failure to ensure this could cause voltage differentials between pins exceeding the device's Absolute Maximum Ratings, thereby leading to latch-up or permanent damage.

PROPAGATION DELAY-RELATED PARAMETERS

Propagation delay is a parameter that describes the length of time it takes for a logic signal to propagate through a component. The propagation delay to a logic low output can differ from the propagation delay to logic high.



Pulse width distortion is the maximum difference between these two propagation delay values and is an indication of how accurately the input signal's timing is preserved.

Channel-to-channel matching refers to the maximum amount the propagation delay differs among channels within a single ADuM240x component.

Propagation delay skew refers to the maximum amount the propagation delay differs among multiple ADuM240x components operated under the same conditions.

DC CORRECTNESS AND MAGNETIC FIELD IMMUNITY

Positive and negative logic transitions at the isolator input cause narrow (~1 ns) pulses to be sent via the transformer to the decoder. The decoder is bistable and is therefore either set or reset by the pulses, indicating input logic transitions. In the absence of logic transitions at the input for more than ~1 μ s, a periodic set of refresh pulses indicative of the correct input state are sent to ensure dc correctness at the output. If the decoder receives no internal pulses for more than approximately 5 μ s, the input side is assumed to be without power or nonfunctional; in which case, the isolator output is forced to a default state (see Table 11) by the watchdog timer circuit.

The limitation on the ADuM240x's magnetic field immunity is set by the condition in which induced voltage in the transformer's receiving coil is large enough to either falsely set or reset the decoder. The following analysis defines the conditions under which this can occur. The 3 V operating condition of the ADuM240x is examined because it represents the most susceptible mode of operation.

The pulses at the transformer output have an amplitude greater than 1.0 V. The decoder has a sensing threshold at about 0.5 V, therefore establishing a 0.5 V margin in which induced voltages can be tolerated. The voltage induced across the receiving coil is given by

 $V = (-d\beta/dt) \Sigma \prod r_n^2; n = 1, 2, \dots, N$

where:

 β is the magnetic flux density (gauss). N is the number of turns in the receiving coil.

 r_n is the radius of the nth turn in the receiving coil.

Given the geometry of the receiving coil in the ADuM240x and an imposed requirement that the induced voltage be at most 50% of the 0.5 V margin at the decoder, a maximum allowable magnetic field is calculated as shown in Figure 19.

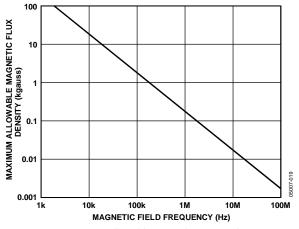
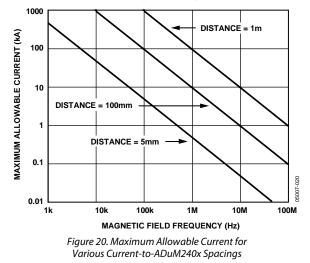


Figure 19. Maximum Allowable External Magnetic Flux Density

For example, at a magnetic field frequency of 1 MHz, the maximum allowable magnetic field of 0.2 kgauss induces a voltage of 0.25 V at the receiving coil. This is about 50% of the sensing threshold and does not cause a faulty output transition. Similarly, if such an event were to occur during a transmitted pulse (and was of the worst-case polarity), it would reduce the received pulse from >1.0 V to 0.75 V—still well above the 0.5 V sensing threshold of the decoder.

The preceding magnetic flux density values correspond to specific current magnitudes at given distances away from the ADuM240x transformers. Figure 20 expresses these allowable current magnitudes as a function of frequency for selected distances. As can be seen, the ADuM240x is immune and can be affected only by extremely large currents operated at high frequency and very close to the component. For the 1 MHz example noted, place a 0.5 kA current 5 mm away from the ADuM240x to affect the component's operation.



Note that at combinations of strong magnetic field and high frequency, any loops formed by printed circuit board traces could induce sufficiently large error voltages to trigger the thresholds of succeeding circuitry. Care should be taken in the layout of such traces to avoid this possibility.

POWER CONSUMPTION

The supply current at a given channel of the ADuM240x isolator is a function of the supply voltage, the data rate of the channel, and the output load of the channel.

For each input channel, the supply current is given by:

$$I_{DDI} = I_{DDI(Q)} \qquad \qquad f \le 0.5 f_r$$

$$I_{DDI} = I_{DDI(D)} \times (2f - f_r) + I_{DDI(Q)}$$
 $f > 0.5f$

For each output channel, the supply current is given by:

$$\begin{split} I_{DDO} &= I_{DDO(Q)} & f \leq 0.5 f_r \\ I_{DDO} &= (I_{DDO(D)} + (0.5 \times 10^{-3} \times C_L V_{DDO}) \times (2f - f_r) + I_{DDO(Q)} \\ & f > 0.5 f_r \end{split}$$

where:

*I*_{DDI (D)}, *I*_{DDO (D)} are the input and output dynamic supply currents per channel (mA/Mbps).

*C*_{*L*} is the output load capacitance (pF).

 V_{DDO} is the output supply voltage (V).

f is the input logic signal frequency (MHz, half of the input data rate, NRZ signaling).

 f_r is the input stage refresh rate (Mbps).

*I*_{DDI (Q)}, *I*_{DDO (Q)} are the specified input and output quiescent supply currents (mA).

To calculate the total I_{DD1} and I_{DD2} , the supply currents for each input and output channel corresponding to I_{DD1} and I_{DD2} are calculated and totaled. Figure 8 and Figure 9 provide per channel supply currents as a function of data rate for an unloaded output condition. Figure 10 provides per channel supply current as a function of data rate for a 15 pF output condition. Figure 11 through Figure 15 provide the total I_{DD1} and I_{DD2} as a function of data rate for the ADuM2400/ADuM2401/ ADuM2402 channel configurations.

INSULATION LIFETIME

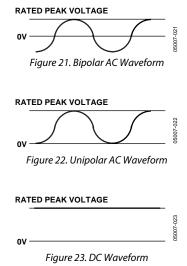
All insulation structures eventually break down when subjected to voltage stress over a sufficiently long period. The rate of insulation degradation is dependent on the characteristics of the voltage waveform applied across the insulation. In addition to the testing performed by the regulatory agencies, Analog Devices carries out an extensive set of evaluations to determine the lifetime of the insulation structure within the ADuM240x.

Analog Devices performs accelerated life testing using voltage levels higher than the rated continuous working voltage. Acceleration factors for several operating conditions are determined. These factors allow calculation of the time to failure at the actual working voltage. The values shown in Table 10 summarize the peak voltage for 50 years of service life for a bipolar ac operating condition and the maximum CSA/VDE approved working voltages. In many cases, the approved working voltage is higher than the 50-year service life voltage. Operation at these high working voltages can lead to shortened insulation life in some cases.

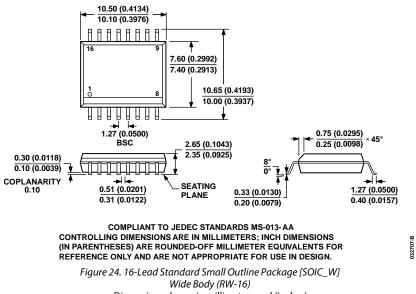
The insulation lifetime of the ADuM240x depends on the voltage waveform type imposed across the isolation barrier. The *i*Coupler insulation structure degrades at different rates, depending on whether the waveform is bipolar ac, unipolar ac, or dc. Figure 21, Figure 22, and Figure 23 illustrate these different isolation voltage waveforms.

Bipolar ac voltage is the most stringent environment. The goal of a 50-year operating lifetime under the ac bipolar condition determines Analog Devices recommended maximum working voltage. In the case of unipolar ac or dc voltage, the stress on the insulation is significantly lower. This allows operation at higher working voltages while still achieving a 50-year service life. The working voltages listed in Table 10 can be applied while maintaining the 50-year minimum lifetime, provided the voltage conforms to either the unipolar ac or dc voltage cases. Any cross-insulation voltage waveform that does not conform to Figure 22 or Figure 23 should be treated as a bipolar ac waveform and its peak voltage should be limited to the 50-year lifetime voltage value listed in Table 10.

Note that the voltage presented in Figure 22 is shown as sinusoidal for illustration purposes only. It is meant to represent any voltage waveform varying between 0 V and some limiting value. The limiting value can be positive or negative, but the voltage cannot cross 0 V.



OUTLINE DIMENSIONS



Dimensions shown in millimeters and (inches)

ORDERING GUIDE

Model	Number of Inputs, V _{DD1} Side	Number of Inputs, V _{DD2} Side	Maximum Data Rate (Mbps)	Maximum Propagation Delay, 5 V (ns)	Maximum Pulse Width Distortion (ns)	Temperature Range	Package Description	Package Option
ADuM2400ARWZ ^{1, 2}	4	0	1	100	40	-40°C to +105°C	16-Lead SOIC_W	RW-16
ADuM2400BRWZ ^{1, 2}	4	0	10	50	3	-40°C to +105°C	16-Lead SOIC_W	RW-16
ADuM2400CRWZ ^{1, 2}	4	0	90	32	2	-40°C to +105°C	16-Lead SOIC_W	RW-16
ADuM2401ARWZ ^{1,2}	3	1	1	100	40	-40°C to +105°C	16-Lead SOIC_W	RW-16
ADuM2401BRWZ ^{1, 2}	3	1	10	50	3	-40°C to +105°C	16-Lead SOIC_W	RW-16
ADuM2401CRWZ ^{1,2}	3	1	90	32	2	-40°C to +105°C	16-Lead SOIC_W	RW-16
ADuM2402ARWZ ^{1,2}	2	2	1	100	40	-40°C to +105°C	16-Lead SOIC_W	RW-16
ADuM2402BRWZ ^{1, 2}	2	2	10	50	3	-40°C to +105°C	16-Lead SOIC_W	RW-16
ADuM2402CRWZ ^{1,2}	2	2	90	32	2	-40°C to +105°C	16-Lead SOIC_W	RW-16

¹ Tape and reel is available. The addition of an -RL suffix designates a 13" (1,000 units) tape and reel option.

 2 Z = RoHS Compliant Part.

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